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substantially filling said contact hole in said overlayer with a second conductive material which differs in composition from said first conductive layer and which contacts said first conductive material.

35. A process for making a semiconductor device having an improved contact to a conductive layer comprising:

providing a first layer of material and forming an opening therein, said opening including sidewalls;

forming a layer of a first conductive material on said first layer of material and along the surfaces of said sidewalls of said opening to form a localized thick region, wherein said first conductive material forms spacers on said sidewalls;

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forming an overlayer of material on said layer of said first conductive material;

forming a contact hole in said overlayer and in said localized thick region which communicates with said layer of said first conductive material, wherein said contact hole is etched in said overlayer and an overetch amount of said layer of said first conductive material, wherein said overetch amount is an amount necessary to account for variations in the thickness of said overlayer in forming said first layer of material and said layer of said first conductive material; and

substantially filling said contact hole in said overlayer with a second conductive material which differs in composition from said first conductive layer and which contacts at least said spacers.

Please cancel claim 47.

48. A process for making a semiconductor device comprising:

forming a conductive layer having a first thickness over an underlayer;

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forming a thick region of said conductive layer having a second thickness greater than said first thickness;